

a) being between said first and second speeds for a third predetermined time, whereby said resist material is evenly spread across said wafer --.

IN THE CLAIMS:

Please cancel Claims 1-4 without prejudice.

Please add new Claims 5-25 as follows:

5. A method of depositing a resist material on a semiconductor wafer comprising the steps of:

placing a resist material at a central portion of said semiconductor wafer;

spinning said wafer at a first speed for a first predetermined time;

spinning said wafer at a second speed which is less than said first speed for a second predetermined time; and

spinning said wafer at a third speed, said third speed being between said first and second speeds for a third predetermined time, whereby said resist material is evenly spread across said wafer.

6. The method of Claim 5 further comprising the step of spinning said wafer at a fourth speed for a fourth predetermined time before said placing step for removing dust on said wafer.

7. The method of Claim 5 wherein said first speed is in the range of substantially 3000-3800 rpm.

8. The method of Claim 5 wherein said second speed is substantially 800 rpm.

9. The method of Claim 7 wherein said second speed is substantially 800 rpm.

19
10. The method of Claim ~~5~~¹ wherein said third speed is substantially 2900 rpm.

124
11. The method of Claim ~~4~~⁴ wherein said third speed is substantially 2900 rpm.

17
12. The method of Claim ~~8~~¹⁶ wherein said third speed is substantially 2900 rpm.

13
13. The method of Claim ~~8~~¹² wherein said third speed is substantially 2900 rpm.

2
14. The method of Claim ~~6~~² wherein said first speed is in the range of substantially 3000-3800 rpm.

16
15. The method of Claim ~~8~~² wherein said second speed is substantially 800 rpm.

4
16. The method of Claim ~~14~~³ wherein said second speed is substantially 800 rpm.

9
17. The method of Claim ~~8~~² wherein said third speed is substantially 2900 rpm.

8
18. The method of Claim ~~14~~³ wherein said third speed is substantially 2900 rpm.

7
19. The method of Claim ~~18~~⁶ wherein said third speed is substantially 2900 rpm.

~~5~~
20. The method of Claim ~~16~~⁴ wherein said third speed is substantially 2900 rpm.

~~21~~¹
The method of Claim ~~5~~¹ wherein said semiconductor wafer is rotated at a speed in the range of substantially 1000-1500 rpm during said placing step.

~~10~~
22. The method of Claim ~~6~~² wherein said semiconductor wafer is rotated at a speed in the range of substantially 1000-1500 rpm during said placing step.

~~15~~
23. The method of Claim ~~7~~¹¹ wherein said semiconductor wafer is rotated at a speed in the range of substantially 1000-1500 rpm during said placing step.

~~18~~
24. The method of Claim ~~8~~¹⁶ wherein said semiconductor wafer is rotated at a speed in the range of substantially 1000-1500 rpm during said placing step.

~~20~~
25. The method of Claim ~~10~~¹⁹ wherein said semiconductor wafer is rotated at a speed in the range of substantially 1000-1500 rpm during said placing step.
